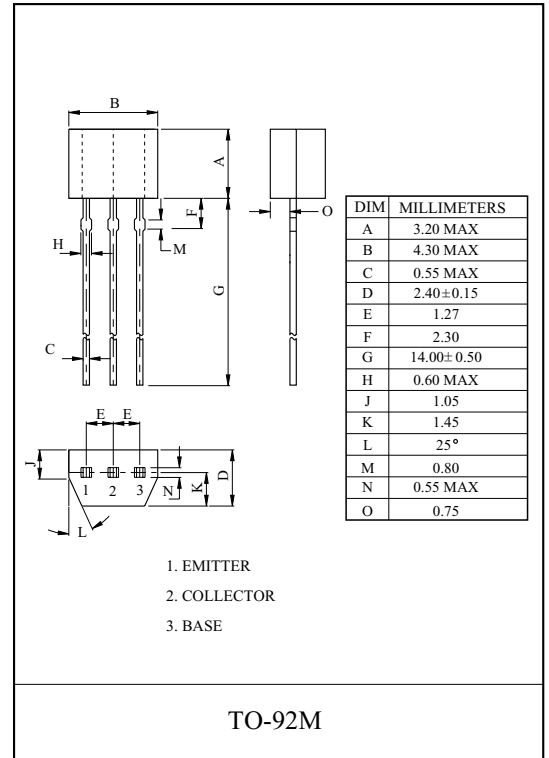
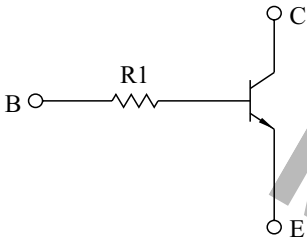


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

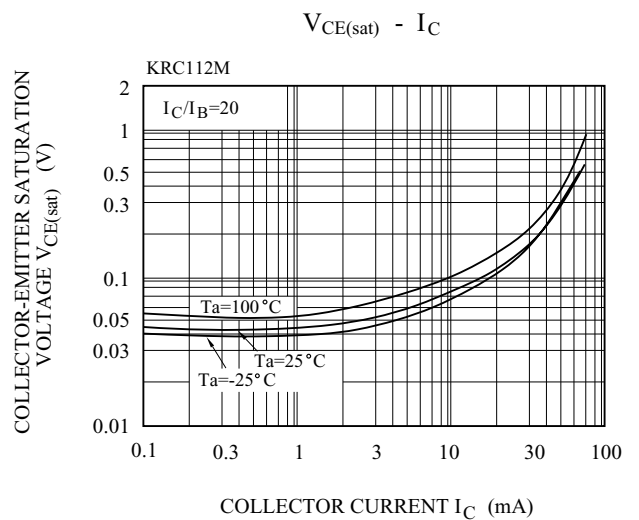
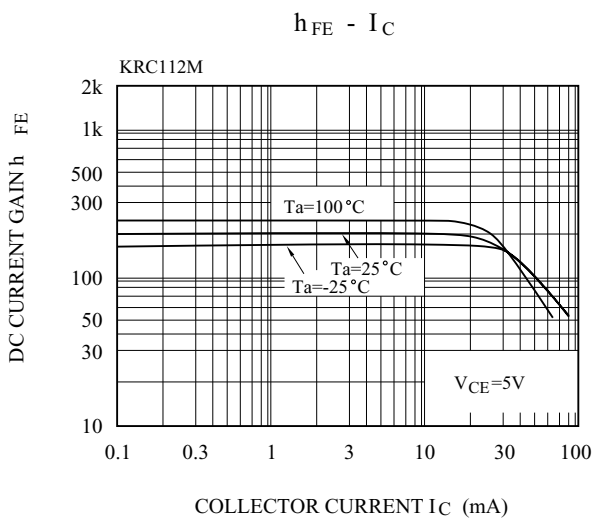
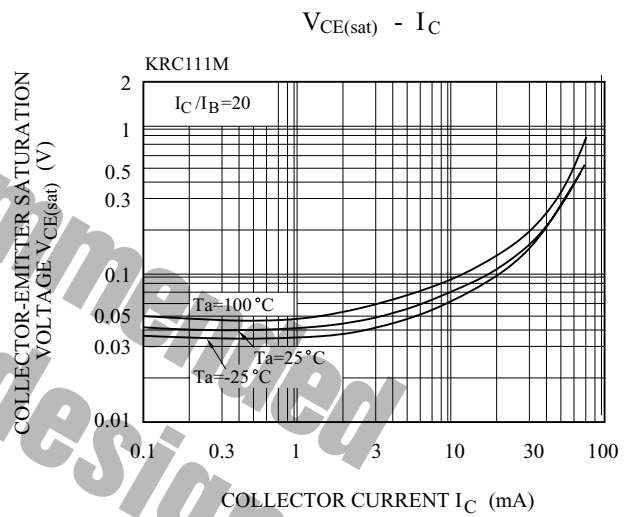
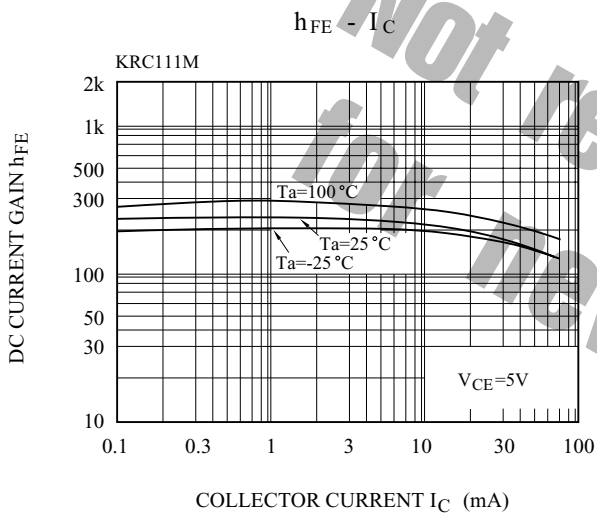
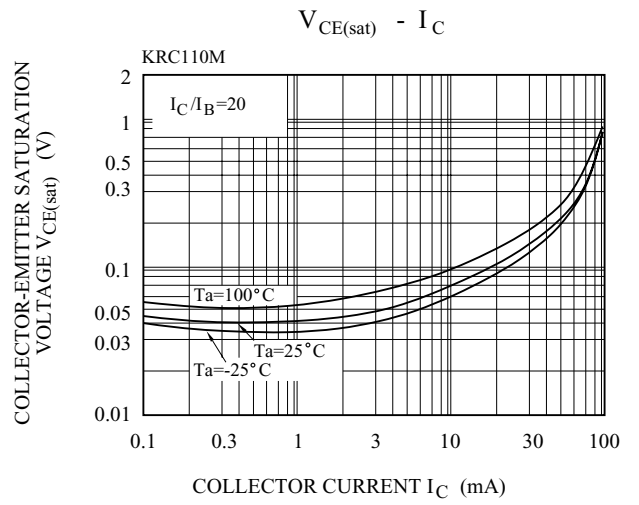
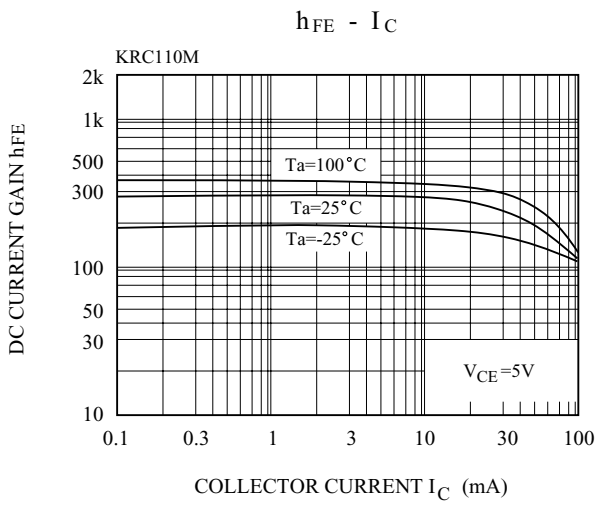
KRC110M~KRC114M

ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current		I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	100	nA	
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	nA	
DC Current Gain		h_{FE}	$V_{CE}=5V, I_C=1mA$	120	-	-		
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	-	0.1	0.3	V	
Transition Frequency		f_T^*	$V_{CE}=10V, I_C=5mA$	-	250	-	MHz	
Switching Time	Rise Time	KRC110M	t_r	$V_O=5V$ $V_{IN}=5V$ $R_I=1k$	-	0.025	-	μs
		KRC111M			-	0.03	-	
		KRC112M			-	0.3	-	
		KRC113M			-	0.06	-	
		KRC114M			-	0.11	-	
	Storage Time	KRC110M			-	3.0	-	
		KRC111M			-	2.0	-	
		KRC112M			-	6.0	-	
		KRC113M			-	4.0	-	
		KRC114M			-	5.0	-	
	Fall Time	KRC110M			-	0.2	-	
		KRC111M			-	0.12	-	
		KRC112M			-	2.0	-	
		KRC113M			-	0.9	-	
		KRC114M			-	1.4	-	
Input Resistor	KRC110M		R_I	-	3.29	4.7	6.11	k
	KRC111M				7	10	13	
	KRC112M				70	100	130	
	KRC113M				15.4	22	28.6	
	KRC114M				32.9	47	61.1	

Note : * Characteristic of Transistor Only.

KRC110M~KRC114M



KRC110M~KRC114M

